

Typ	L #	Hit	S arch T xt	DB	Tim Stamp	C mm nts	Err r D finlti n	Err rs
7 BRS	L7	956	gallium adj nitrid	USPAT	2002/02/28 15:04			0
8 BRS	L8	78	gallium adj nitrogen	USPAT	2002/02/28 15:04			0
9 BRS	L9	3114	gan	USPAT	2002/02/28 15:04			0
10 BRS	L10	412	algan	USPAT	2002/02/28 15:04			0
11 BRS	L11	168	iii adj nitride	USPAT	2002/02/28 15:04			0
12 BRS	L12	102	iii adj v adj nitride	USPAT	2002/02/28 15:05			0
13 BRS	L13	467	(7 8 9 10 11 12).ti,ab.	USPAT	2002/02/28 15:05			0
14 BRS	L14	71	13 and dielectric	USPAT	2002/02/28 15:14			0
15 BRS	L15	10582	sio	USPAT	2002/02/28 15:15			0
16 BRS	L16	34291	sin	USPAT	2002/02/28 15:15			0
17 BRS	L17	6243	sion	USPAT	2002/02/28 15:15			0
18 BRS	L18	495	15 same 16	USPAT	2002/02/28 15:16			0
19 BRS	L19	2	18 and 372/46.ccls.	USPAT	2002/02/28 15:17			0
20 BRS	L20	419	h01s003/18 and gan	JPO	2002/02/28 15:17			0
21 BRS	L21	26	h01s003/18 and gan and	JPO	2002/02/28 15:23			0
22 BRS	L22	52	gan and sio	JPO	2002/02/28 15:23			0
23 BRS	L24	1	23 and sin	JPO	2002/02/28 15:24			0

	Typ	L #	Hits	S ar h Text	DB	Tim Stamp	Comm nt	Error D finlti n	Err rs
24	BRS	L23 26		22 not 21	JPO	2002/02/28 15:28			0
25	BRS	L25 853		h01s003/18 and (nitride or nitrogen)	JPO	2002/02/28 15:29			0
26	BRS	L26 147		h01s003/18 and (nitride or nitrogen) and (sio or tio or insulat\$ or dielectric)	JPO	2002/02/28 15:30			0
27	BRS	L27 28		h01s003/18 and (gan or algan or ingaasn or gaasn or bn)	JPO	2002/02/28 15:32			0
28	BRS	L29 823		sio with sin	JPO	2002/02/28 15:34			0
29	BRS	L30 336		29 and ((semiconducto r or diode\$1) near2 (laser\$ or device\$))	JPO	2002/02/28 15:34			0
30	BRS	L31 1		sio with sin with grad\$	JPO	2002/02/28 15:34			0
31	BRS	L32 11057		oxide with nitride	JPO	2002/02/28 15:34			0
32	BRS	L33 42		32 and (h01s003/18 or h01s005/00)	JPO	2002/02/28 15:40			0
33	BRS	L34 0		oxynitride and gan	JPO	2002/02/28 15:40			0
34	BRS	L35 0		oxynitride and algan	JPO	2002/02/28 15:40			0

	Typ	L #	Hits	S arch T xt	DBs	Tim Stamp	C mm nts	Error D flntli n	Errors
35	BRS	L36 4		oxynitrid and algan	USPAT	2002/02/28 15:41			0
36	BRS	L37 8		oxynitride and 372/46\$.ccls.	USPAT	2002/02/28 15:46			0
37	BRS	L38 153		372/46,45.ccls. and gan	USPAT	2002/02/28 15:46			0
38	BRS	L39 331928		LD or LED or VCSEL or VCSELS or diode or diodes or RCLED or RCLEDs or RCPD or RCPDs or LDs or LEDs	USPAT	2002/02/28 16:07			0
39	BRS	L40 19092		gan or aln or inn or bn or tln	USPAT	2002/02/28 16:07			0
40	BRS	L41 3908		39 and 40	USPAT	2002/02/28 16:08			0
41	BRS	L42 2154		41 and (oxynitride or oxide or nitride)	USPAT	2002/02/28 16:08			0
42	BRS	L43 57		41 and (oxynitride and oxide and nitride)	USPAT	2002/02/28 16:40			0
43	BRS	L44 8		372/46.ccls. and oxynitride	USPAT	2002/02/28 16:40			0
44	BRS	L45 0		44 and gan	USPAT	2002/02/28 16:40			0
45	BRS	L46 50		oxynitride and gan	USPAT	2002/02/28 16:45			0
46	BRS	L47 9		sion and 372/46. cls.	USPAT	2002/02/28 16:45			0

	Typ	L #	Hits	S arch T xt	DB	Tim Stamp	C mm nts	Err r D finiti n	Err rs
47	BRS	L48 0		si n and 372/46.ccls. and nitride	USPAT	2002/02/28 16:45		0	
48	BRS	L49 0		sion and 372/46.ccls. and gan	USPAT	2002/02/28 16:45		0	